



#### 50V N-Channel Enhancement Mode MOSFET - ESD Protected

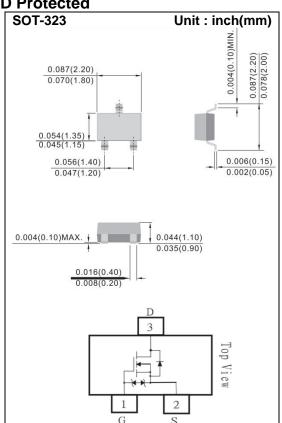
Voltage 50 V Current 360mA

#### **Features**

- RDS(ON), VGS@10V, ID@500mA<1.6Ω
- RDS(ON), VGS@4.5V, ID@200mA<2.5Ω</li>
- RDS(ON), VGS@2.5V, ID@100mA<4.5Ω</li>
- Advanced Trench Process Technology
- Specially Designed for Battery Operated Systems, Solid-State Relays Drivers: Relay, Displays, Memories, etc.
- ESD Protected 2KV HBM
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std. (Halogen Free)

#### **Mechanical Data**

- Case: SOT-323 Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.00018 ounces, 0.005 grams



## **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

| PARAMETER  |                      | SYMBOL          | LIMIT       | UNITS |
|--|----------------------|-----------------|-------------|-------|
| Drain-Source Voltage                             |                      | V <sub>DS</sub> | 50          | V     |
| Gate-Source Voltage                              |                      | $V_{GS}$        | <u>+</u> 20 | V     |
| Continuous Drain Current                         |                      | I <sub>D</sub>  | 360         | mA    |
| Pulsed Drain Current                             |                      | I <sub>DM</sub> | 1200        | mA    |
| Power Dissipation                                | T <sub>A</sub> =25°C | $P_D$           | 236         | mW    |
|  | Derate above 25°C    |                 | 1.89        | mW/°C |
| Operating Junction and Storage Temperature Range |                      | $T_J, T_{STG}$  | -55~150     | °C    |
| Typical Thermal resistance                       |                      |                 |             |       |
| - Junction to Ambient (Note 3)                   |                      | $R_{\theta JA}$ | 530         | °C/W  |

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# **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

| PARAMETER                        | SYMBOL              | TEST CONDITION   | MIN. | TYP.         | MAX.        | UNITS |
|----------------------------------|---------------------|--|------|--------------|-------------|-------|
| Static                           |                     |  |      |              |             |       |
| Drain-Source Breakdown Voltage   | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V,I <sub>D</sub> =250uA  | 50   | -            | -           | V     |
| Gate Threshold Voltage           | $V_{GS(th)}$        | $V_{DS}=V_{GS}$ , $I_{D}=250uA$  | 0.8  | 1.0          | 1.5         | V     |
| Drain-Source On-State Resistance | R <sub>DS(on)</sub> | V <sub>GS</sub> =10V,I <sub>D</sub> =500mA   | -    | 0.96         | 1.6         | Ω     |
|                                  |                     | V <sub>GS</sub> =4.5V,I <sub>D</sub> =200mA  | -    | 1.25         | 2.5         |       |
|                                  |                     | V <sub>GS</sub> =2.5V,I <sub>D</sub> =100mA  | -    | 2.73         | 4.5         |       |
| Zero Gate Voltage Drain Current  | I <sub>DSS</sub>    | $V_{DS}$ =50V, $V_{GS}$ =0V  | -    | 0.01         | 1           | uA    |
| Gate-Source Leakage Current      | $I_{GSS}$           | V <sub>GS</sub> = <u>+</u> 20V,V <sub>DS</sub> =0V   | -    | <u>+</u> 3.0 | <u>+</u> 10 | uA    |
| Dynamic                          |                     |  |      |              |             |       |
| Total Gate Charge                | $Q_g$               | V <sub>DS</sub> =25V, I <sub>D</sub> =250mA,<br>V <sub>GS</sub> =4.5V <sup>(Note 1,2)</sup>                        | -    | 0.63         | 1           | nC    |
| Gate-Source Charge               | $Q_gs$              |  | -    | 0.2          | -           |       |
| Gate-Drain Charge                | $Q_gd$              |  | -    | 0.23         | -           |       |
| Input Capacitance                | Ciss                | V <sub>DS</sub> =25V, V <sub>GS</sub> =0V,<br>f=1.0MHZ   | -    | 25           | 50          | pF    |
| Output Capacitance               | Coss                |  | -    | 9.5          | 20          |       |
| Reverse Transfer Capacitance     | Crss                | I=1.UIVIHZ   | -    | 2.1          | 5           |       |
| Switching                        |                     |  |      |              |             |       |
| Turn-On Delay Time               | td <sub>(on)</sub>  | \/ O5\/   500 A  | -    | 2.2          | 5           | ns    |
| Turn-On Rise Time                | tr                  | $\begin{array}{l} V_{DD}{=}25V,\ I_{D}{=}500mA,\\ V_{GS}{=}10V,\\ R_{G}{=}6\Omega^{\text{(Note 1,2)}} \end{array}$ |      | 19.2         | 38          |       |
| Turn-Off Delay Time              | td <sub>(off)</sub> |  |      | 6.2          | 12          |       |
| Turn-Off Fall Time               | tf                  |  | -    | 23           | 50          |       |
| Drain-Source Diode               |                     |  |      |              |             |       |
| Maximum Continuous Drain-Source  | Is                  |  | _    | _            | 500         | mA    |
| Diode Forward Current            | .5                  |  |      |              |             |       |
| Diode Forward Voltage            | $V_{\mathtt{SD}}$   | I <sub>S</sub> =500mA, V <sub>GS</sub> =0V   |      | 0.86         | 1.5         | V     |

#### NOTES:

- 1. Pulse width < 300 μs, Duty cycle < 2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejua is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. mounted on a 1 inch square pad of copper





#### **TYPICAL CHARACTERISTIC CURVES**

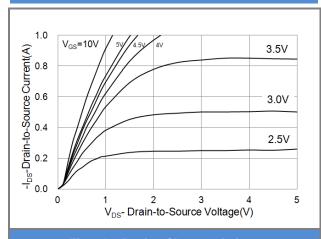
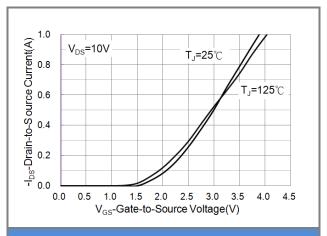


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

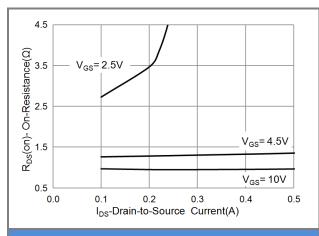


Fig.3 On-Resistance vs. Drain Current

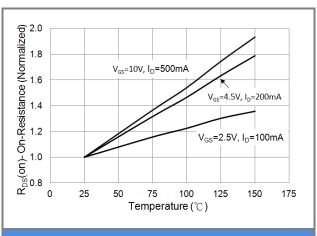


Fig.4 On-Resistance vs. Junction temperature

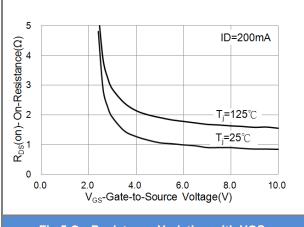
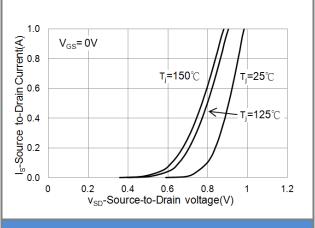


Fig.5 On-Resistance Variation with VGS.



**Fig.6 Body Dlode CharacterIslcs** 



1.4

1.2

Vth-G-S Variance 8.0 8.0 9.0

0.4

-50

-25



50

# **PJC138K**

#### **TYPICAL CHARACTERISTIC CURVES**

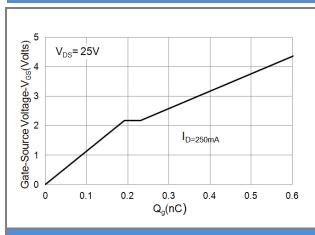
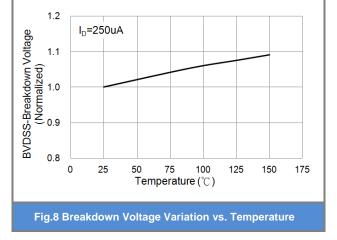


Fig.7 Gate-Charge Characteristics

I<sub>D</sub>=250uA

125



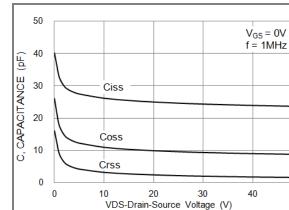
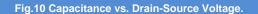


Fig.9 Threshold Voltage Variation with Temperature.

25 50 75 Temperature (°C)



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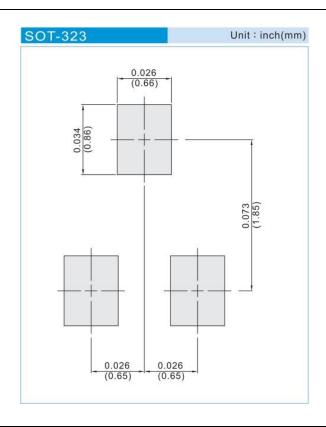




### PART NO PACKING CODE VERSION

| PART NO PACKING  CODE VERSION | Package Type | Packing type       | Marking | Version      |
|-------------------------------|--------------|--------------------|---------|--------------|
| PJC138K_R1_00001              | SOT-323      | 3K pcs / 7" reel   | 8KW     | Halogen free |
| PJC138K_R2_00001              | SOT-323      | 12K pcs / 13" reel | 8KW     | Halogen free |

### **MOUNTING PAD LAYOUT**







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